

MITSUBISHI IGBT MODULES  
**CM600HU-24F**

HIGH POWER SWITCHING USE

**CM600HU-24F**



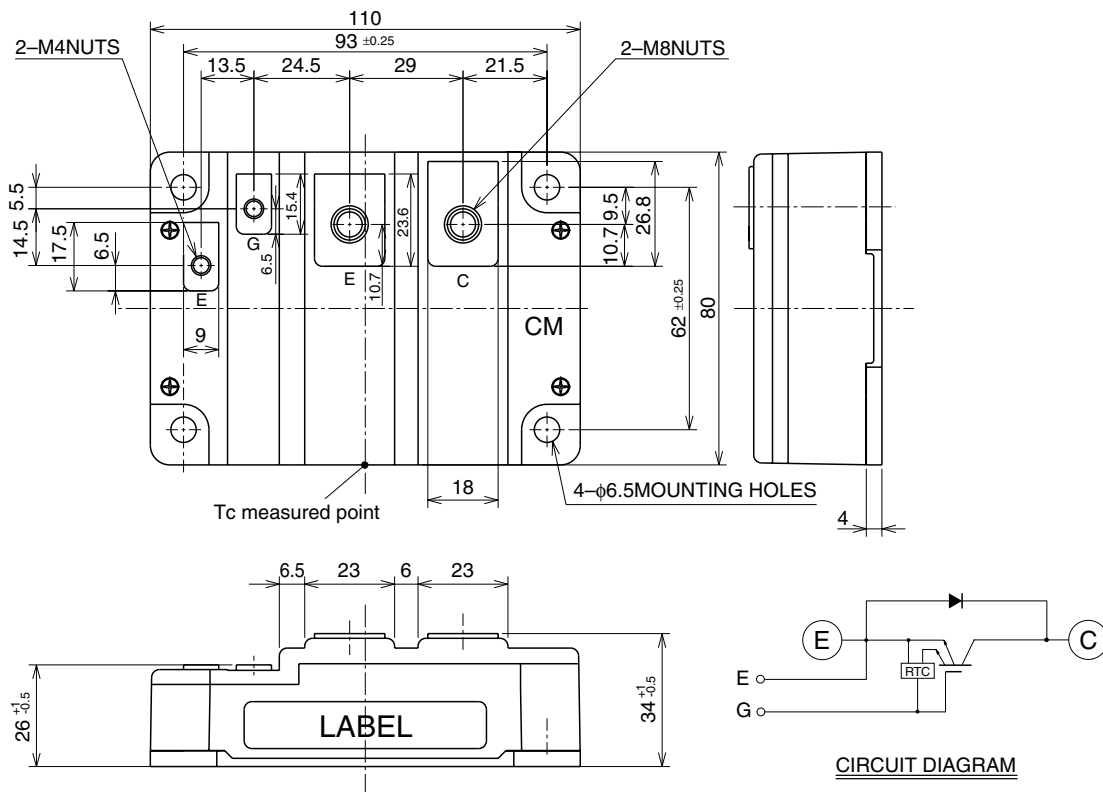
- IC ..... 600A
- VCES ..... 1200V
- Insulated Type
- 1-elements in a pack

**APPLICATION**

General purpose inverters & Servo controls, etc

**OUTLINE DRAWING & CIRCUIT DIAGRAM**

Dimensions in mm



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MAXIMUM RATINGS (Tj = 25°C, unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>CE</sub> S	Collector-emitter voltage	G-E Short	1200	V
V <sub>GE</sub> S	Gate-emitter voltage	C-E Short	±20	V
I <sub>C</sub>	Collector current	T <sub>C</sub> = 25°C	600	A
I <sub>CM</sub>		Pulse (Note 2)	1200	
I <sub>E</sub> (Note 1)	Emitter current	T <sub>C</sub> = 25°C	600	A
I <sub>EM</sub> (Note 1)		Pulse (Note 2)	1200	
P <sub>C</sub> (Note 3)	Maximum collector dissipation	T <sub>C</sub> = 25°C	1900	W
T <sub>j</sub>	Junction temperature		-40 ~ +150	°C
T <sub>stg</sub>	Storage temperature		-40 ~ +125	°C
V <sub>iso</sub>	Isolation voltage	Terminals to base plate, f = 60Hz, AC 1 minute	2500	V <sub>rms</sub>
—	Torque strength	Main terminals M8 screw	8.8 ~ 10.8	N • m
		Mounting M6 screw	3.5 ~ 4.5	N • m
		G(E) Terminal M4 screw	1.3 ~ 1.7	N • m
—	Weight	Typical value	600	g

ELECTRICAL CHARACTERISTICS (Tj = 25°C, unless otherwise specified)

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
I <sub>CES</sub>	Collector cutoff current	V <sub>CE</sub> = V <sub>CE</sub> S, V <sub>GE</sub> = 0V	—	—	2	mA	
V <sub>GE(th)</sub>	Gate-emitter threshold voltage	I <sub>C</sub> = 60mA, V <sub>CE</sub> = 10V	5	6	7	V	
I <sub>GES</sub>	Gate leakage current	±V <sub>GE</sub> = V <sub>GES</sub> , V <sub>CE</sub> = 0V	—	—	80	μA	
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> = 600A, V <sub>GE</sub> = 15V	—	T <sub>j</sub> = 25°C 1.8	2.4	V	
		T <sub>j</sub> = 125°C 1.9		—			
C <sub>ies</sub>	Input capacitance	V <sub>CE</sub> = 10V V <sub>GE</sub> = 0V	—	—	230	nF	
C <sub>oes</sub>	Output capacitance		—	—	10		
C <sub>res</sub>	Reverse transfer capacitance		—	—	6.0		
Q <sub>G</sub>	Total gate charge	V <sub>CC</sub> = 600V, I <sub>C</sub> = 600A, V <sub>GE</sub> = 15V	—	6600	—	nC	
t <sub>d(on)</sub>	Turn-on delay time	V <sub>CC</sub> = 600V, I <sub>C</sub> = 600A V <sub>GE</sub> = ±15V R <sub>G</sub> = 1.0Ω, Inductive load	—	—	300	ns	
t <sub>r</sub>	Turn-on rise time		—	—	150		
t <sub>d(off)</sub>	Turn-off delay time		—	—	800		
t <sub>f</sub>	Turn-off fall time		—	—	300		
t <sub>rr</sub> (Note 1)	Reverse recovery time		I <sub>E</sub> = 600A	—	—		500
Q <sub>rr</sub> (Note 1)	Reverse recovery charge		—	43.2	—		μC
V <sub>EC</sub> (Note 1)	Emitter-collector voltage	I <sub>E</sub> = 600A, V <sub>GE</sub> = 0V	—	—	3.2	V	
R <sub>th(j-c)Q</sub>	Thermal resistance*1	IGBT part	—	—	0.063	K/W	
R <sub>th(j-c)R</sub>		FWDi part	—	—	0.075		
R <sub>th(c-f)</sub>	Contact thermal resistance	Case to heat sink, Thermal compound applied*2	—	0.015	—		
R <sub>th(j-c)Q</sub>	Thermal resistance	Case temperature measured point is just under the chips	—	—	0.032*3		
R <sub>G</sub>	External gate resistance		1.0	—	10	Ω	

Note 1. I<sub>E</sub>, V<sub>EC</sub>, t<sub>rr</sub>, Q<sub>rr</sub> & die/dt represent characteristics of the anti-parallel, emitter-collector free-wheel diode (FWDi).

2. Pulse width and repetition rate should be such that the device junction temperature (T<sub>j</sub>) does not exceed T<sub>jmax</sub> rating.

3. Junction temperature (T<sub>j</sub>) should not increase beyond 150°C.

4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

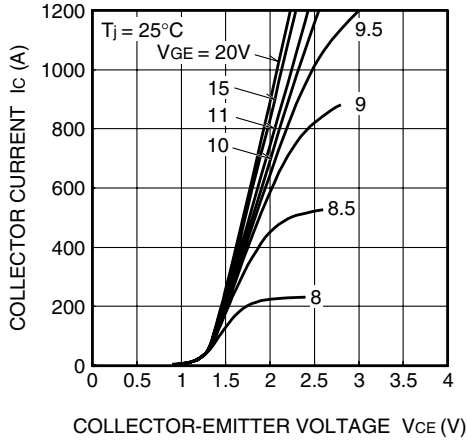
\*1 : Case temperature (T<sub>c</sub>) measured point is indicated in OUTLINE DRAWING.

\*2 : Typical value is measured by using thermally conductive grease of λ = 0.9[W/(m • K)].

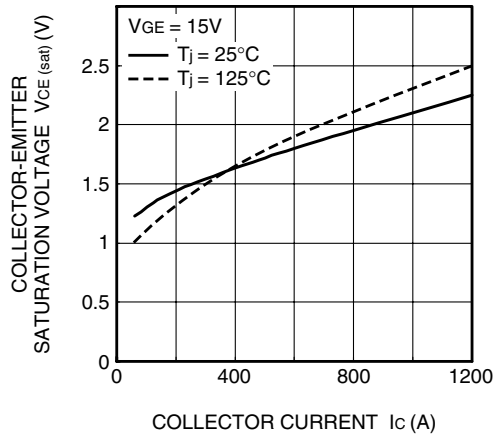
\*3 : If you use this value, R<sub>th(f-a)</sub> should be measured just under the chips.

PERFORMANCE CURVES

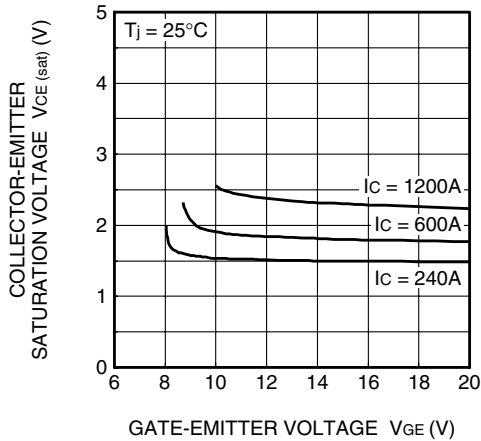
OUTPUT CHARACTERISTICS (TYPICAL)



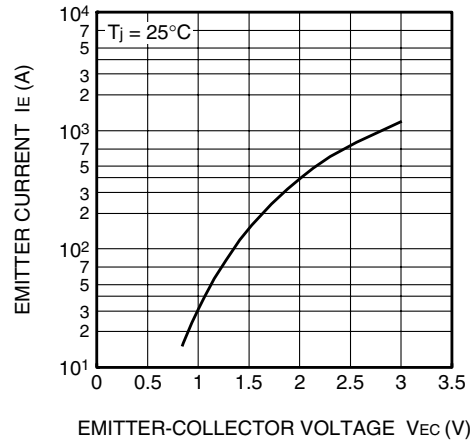
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



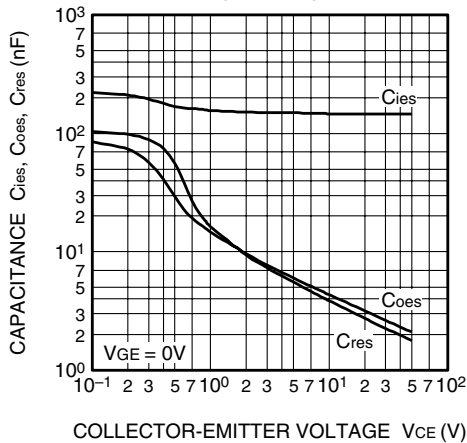
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



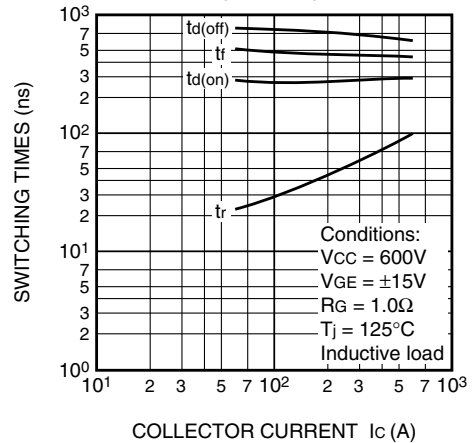
FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



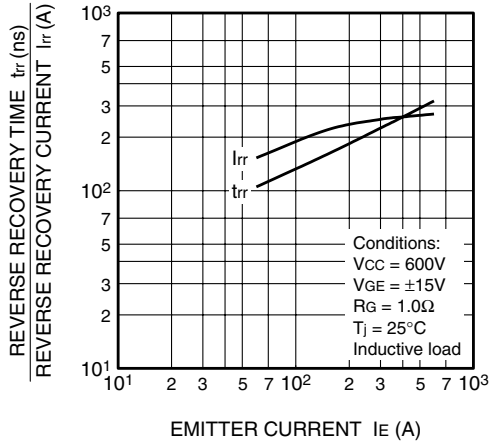
CAPACITANCE- $V_{ce}$  CHARACTERISTICS (TYPICAL)



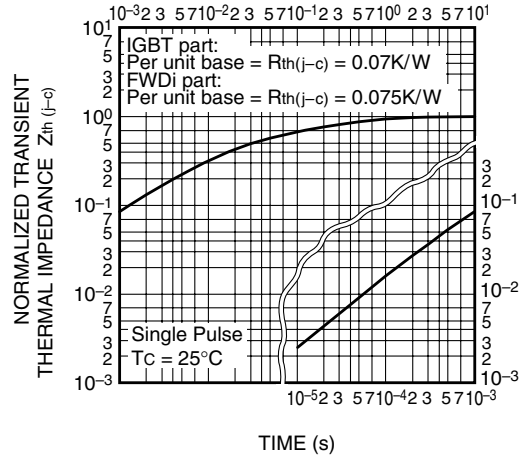
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)



REVERSE RECOVERY CHARACTERISTICS OF FREE-WHEEL DIODE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (IGBT part & FWDi part)



GATE CHARGE CHARACTERISTICS (TYPICAL)

